

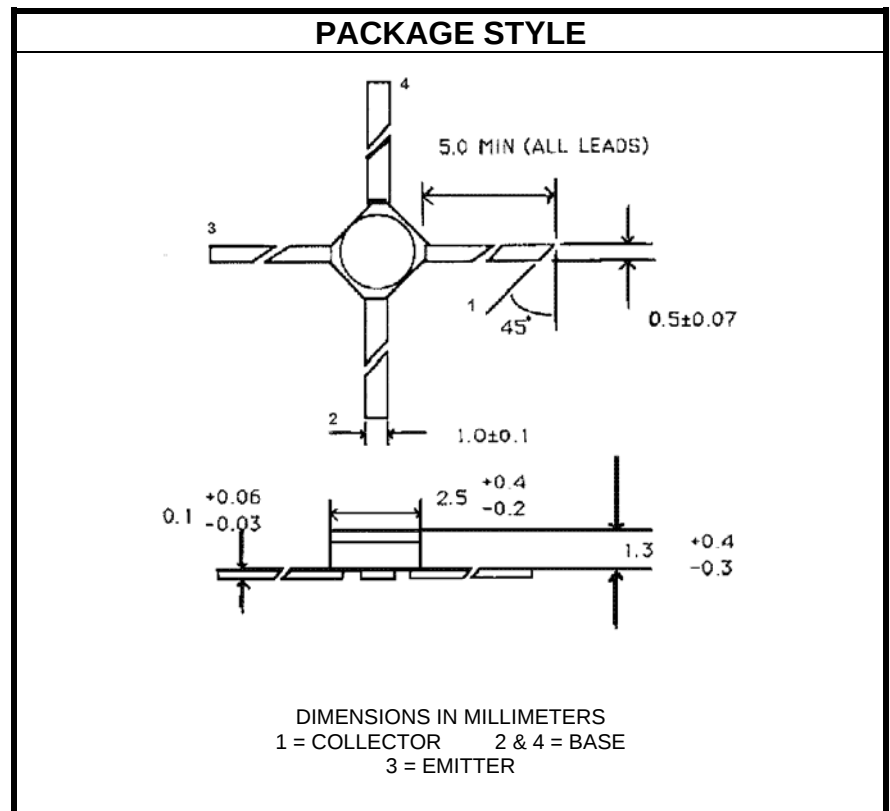
NPN SILICON RF TRANSISTOR

DESCRIPTION:

The **HXTR4101** is a Common Base Device Designed for Oscillator Applications up to 10 GHz.

MAXIMUM RATINGS

I_C	70 mA
V_{EBO}	1.5 V
V_{CEO}	20 V
T_J	300 °C
T_{STG}	-65 °C to 250 °C
P_T	900 mW @ $T_C = 25$ °C



CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
I_{CEO}	$V_{CE} = 15$ V					500	nA
I_{CBO}	$V_{CB} = 15$ V					100	nA
h_{FE}	$V_{CE} = 15$ V	$I_C = 15$ mA		50	120	220	---
P_{osc}	$V_{CB} = 15$ V	$I_C = 30$ mA	$f = 3.0$ GHz	19	21.5		dBm
		$I_C = 30$ mA	$f = 4.3$ GHz		20.5		
		$I_C = 30$ mA	$f = 6.0$ GHz		17		
		$I_C = 30$ mA	$f = 8.0$ GHz		12		
N/C	PHASE NOISE TO CARRIER @ 1.0 KHZ FROM THE CARRIER(SSB)				-50		dBc/Hz
	$f = 4.3$ GHz						